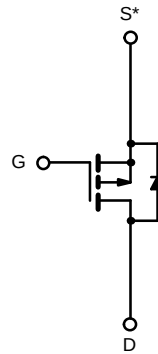
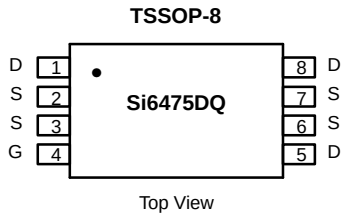




P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.011 @ $V_{GS} = -4.5$ V	-10
	0.0135 @ $V_{GS} = -2.5$ V	-9
	0.017 @ $V_{GS} = -1.8$ V	-8

TrenchFET®
Power MOSFETs

* Source Pins 2, 3, 6 and 7 must be tied common.

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	−12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	−10	−7.8	A
	T _A = 70°C		−8	−6.2	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	−30		
Continuous Source Current (Diode Conduction) ^a		I _S	−1.5	−0.95	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	1.75	1.08	W
	T _A = 70°C		1.14	0.69	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	55	70	$^\circ\text{C/W}$
	Steady State		95	115	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	35	45	

Notes

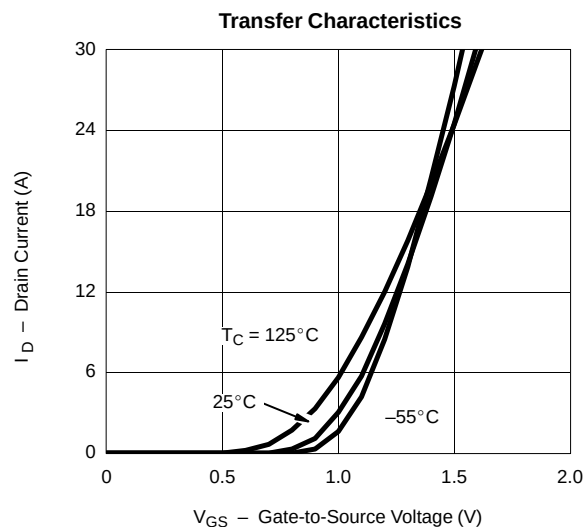
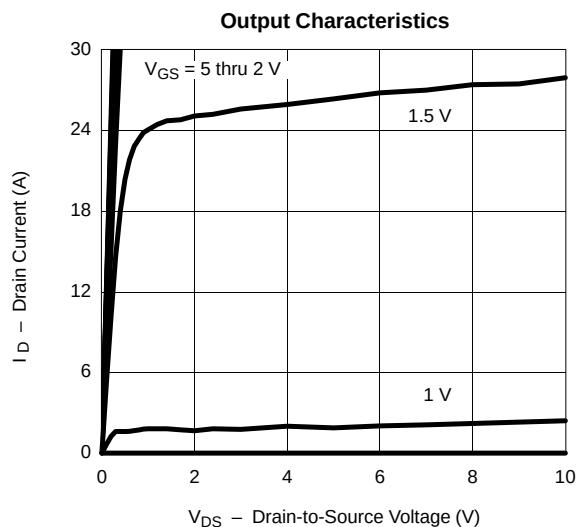
a. Surface Mounted on 1" x 1" FR4 Board.

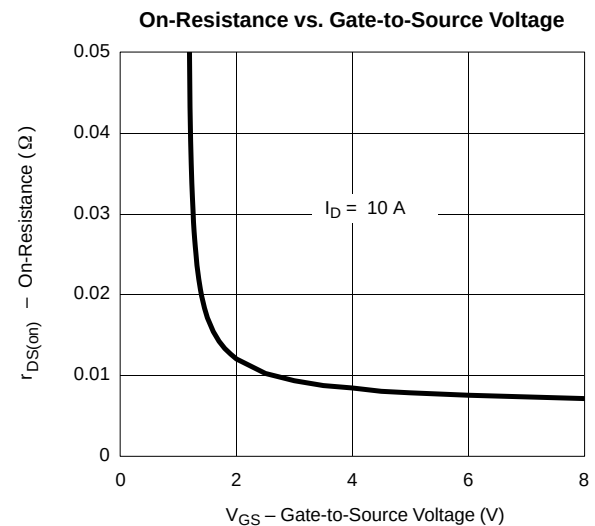
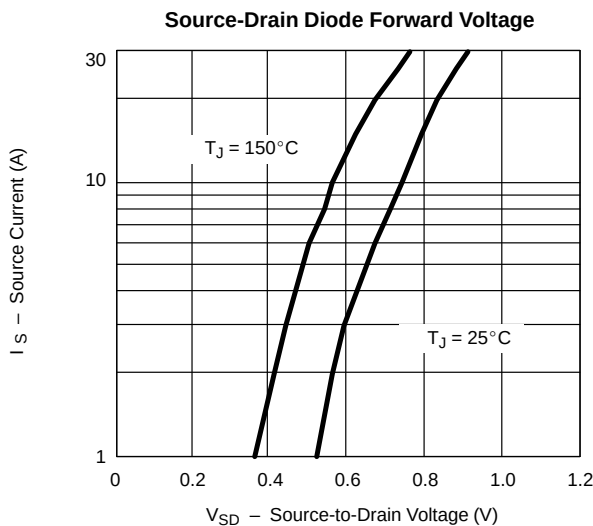
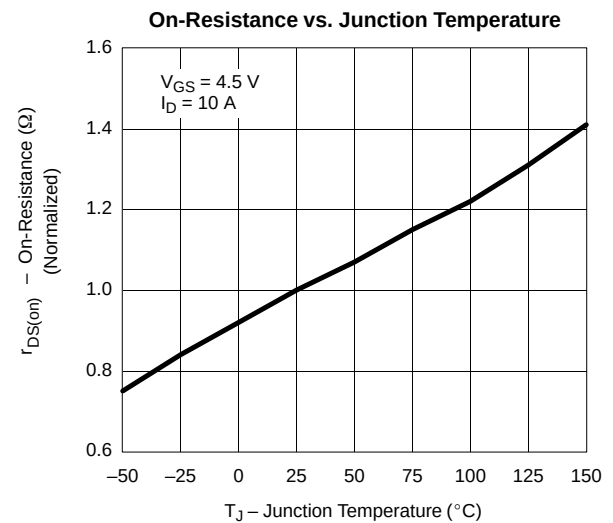
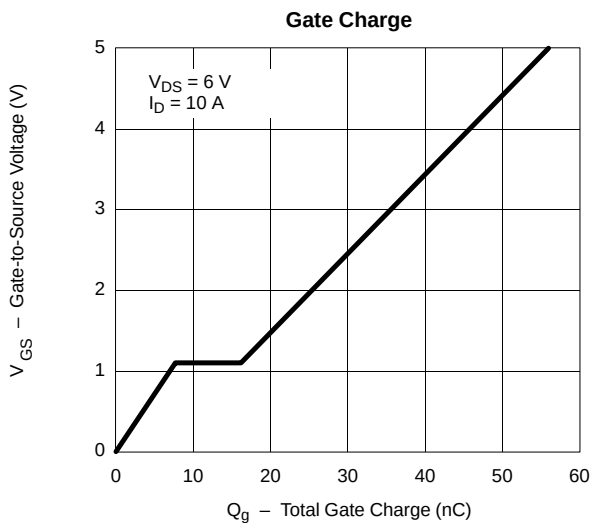
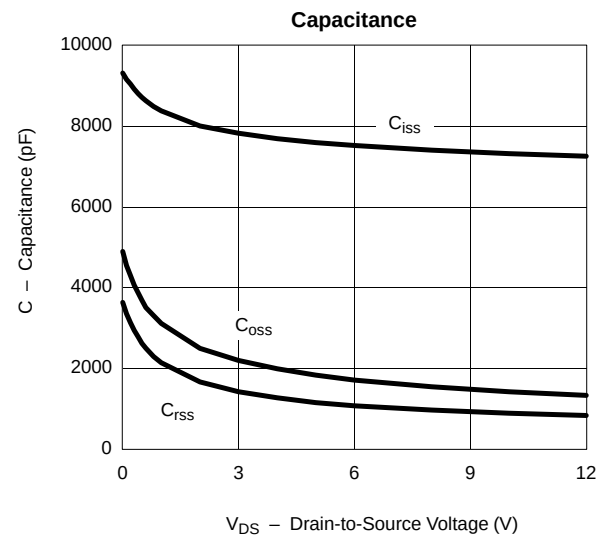
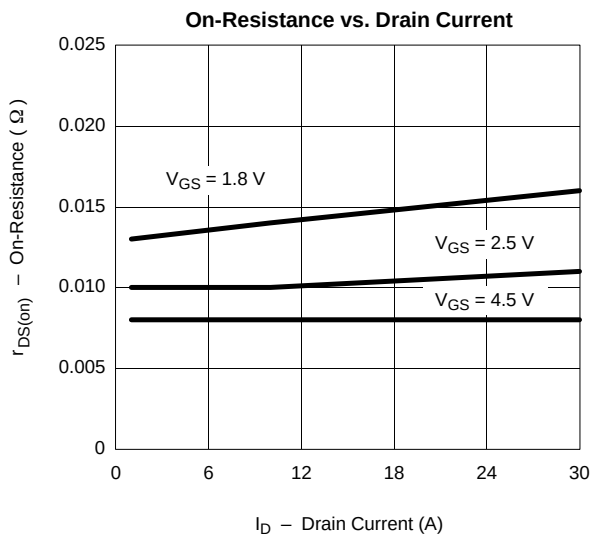
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -5\text{ mA}$	-0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -4.5\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -10\text{ A}$		0.009	0.011	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -9\text{ A}$		0.011	0.0135	
		$V_{GS} = -1.8\text{ V}$, $I_D = -8\text{ A}$		0.014	0.017	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -10\text{ A}$		50		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.5\text{ A}$, $V_{GS} = 0\text{ V}$		-0.68	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -10\text{ A}$		49.5	70	nC
Gate-Source Charge	Q_{gs}			7.7		
Gate-Drain Charge	Q_{gd}			8.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}$, $R_L = 6\ \Omega$ $I_D \approx -1\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_G = 6\ \Omega$		56	85	ns
Rise Time	t_r			62	100	
Turn-Off Delay Time	$t_{d(off)}$			300	450	
Fall Time	t_f			185	270	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		90	150	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

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